



H2N7002KSN

N-CHANNEL TRANSISTOR

Description

N-channel enhancement-mode MOS transistor.

ESD protected

Absolute Maximum Ratings

Drain-Source Voltage	60 V
Drain-Gate Voltage ($R_{GS}=1M\Omega$).....	60 V
Gate-Source Voltage	± 20 V
Continuous Drain Current ($T_A=25^\circ C$) ⁽¹⁾	200 mA
Continuous Drain Current ($T_A=100^\circ C$) ⁽¹⁾	115 mA
Pulsed Drain Current ($T_A=25^\circ C$) ⁽²⁾	800 mA
Storage Temperature.....	-55 to 150 °C
Operating Junction Temperature	-55 to 150 °C
Lead Temperature, for 10 second Soldering	260 °C
Gate Source ESD Rating.....	2KV

Electrical Characteristics ($T_A=25^\circ C$)

Parameter	Symbol	Test Conditions	Min	Typ.	Max	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0, I_D=10\mu A$	60	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=0.25mA$	1	-	2.0	V
Gate Source Leakage Current, Forward	$I_{GSS/F}$	$V_{GS}=+20V, V_{DS}=0$	-	-	10	μA
Gate Source leakage Current, Reverse	$I_{GSS/R}$	$V_{GS}=-20V, V_{DS}=0$	-	-	-10	μA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=48V, V_{GS}=0$	-	-	10	μA
On-State Drain Current	$I_{D(ON)}$	$V_{DS}>2V_{DS(ON)}, V_{GS}=10V$	500	-	-	mA
Static Drain-Source On-State Voltage	$V_{DS(ON)}$	$I_D=50mA, V_{GS}=5V$	-	-	0.375	V
		$I_D=500mA, V_{GS}=10V$	-	-	3.75	V
		$I_D=75mA, V_{GS}=4.5V$	-	-	5.3	Ω
		$I_D=50mA, V_{GS}=5V$	-	-	5.0	Ω
		$I_D=500mA, V_{GS}=10V$	-	-	5.0	Ω
Forward Transconductance	G_{FS}	$V_{DS}>2V_{DS(ON)}, I_D=200mA$	80	-	-	mS
Turn-on Delay Time	$t_{d(on)}$	$(V_{DD}=50V, R_D=250\Omega, V_{GS}=10V, R_G=50\Omega)$	-	20	-	nS
Turn-off Delay Time	$t_{d(off)}$		-	40	-	nS
Input Capacitance	C_{iss}	$V_{DS}=25V, V_{GS}=0, f=1MHz$	-	50	-	pF
Output Capacitance	C_{oss}		-	25	-	pF
Reverse Transfer Capacitance	C_{rss}		-	5	-	pF

(1)The Power Dissipation of the package may result in a continuous drain current.

(2)Pulse Width $\leq 300\mu s$, Duty cycle $\geq 2\%$.

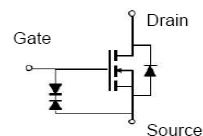
H2N7002KSN Pin Assignment & Symbol



3-Lead Plastic **SOT-323**

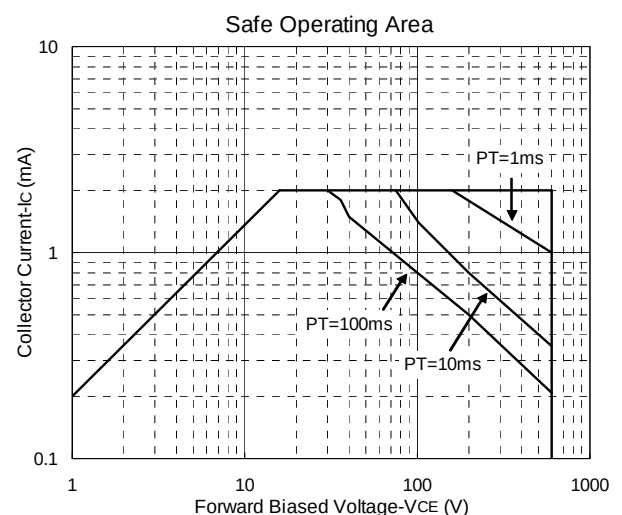
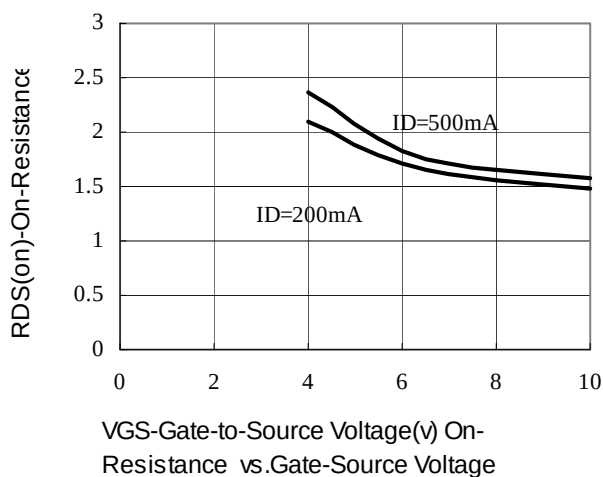
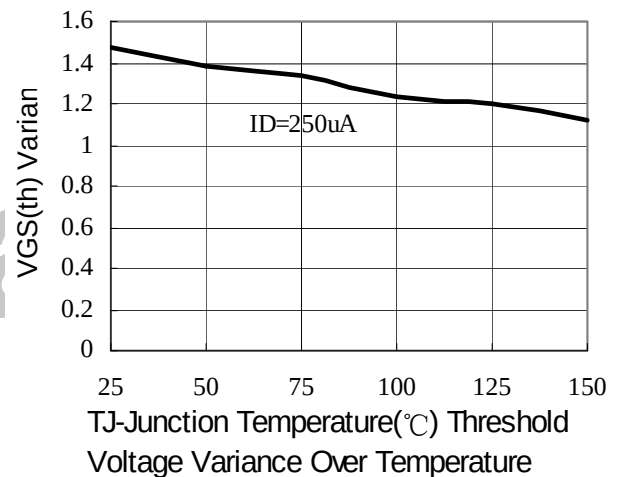
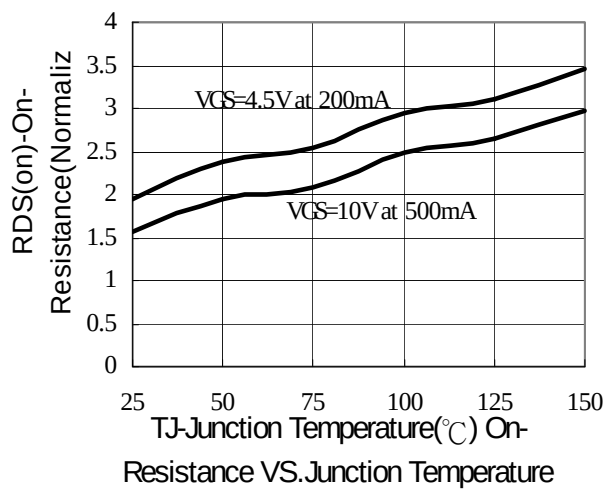
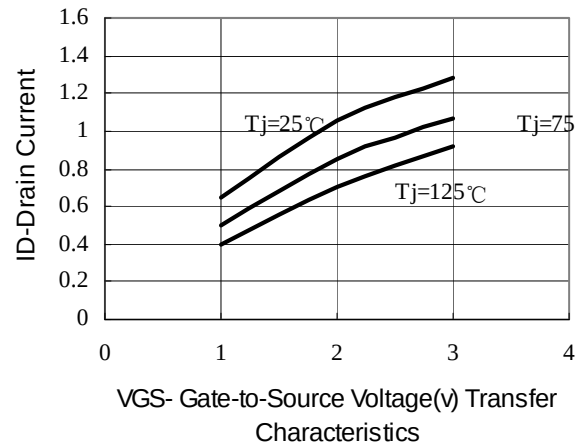
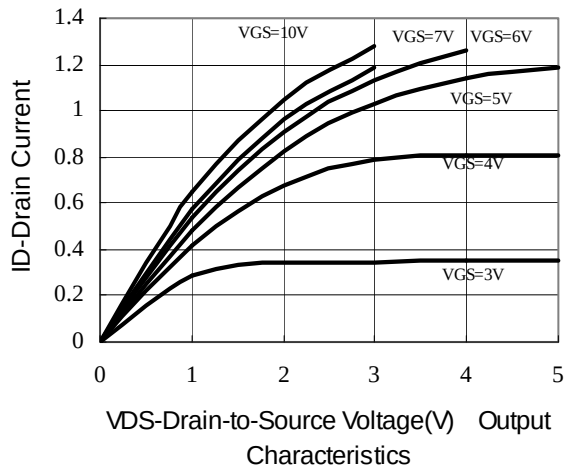
Package Code: SN

Pin 1: Gate 2: Source 3: Drain



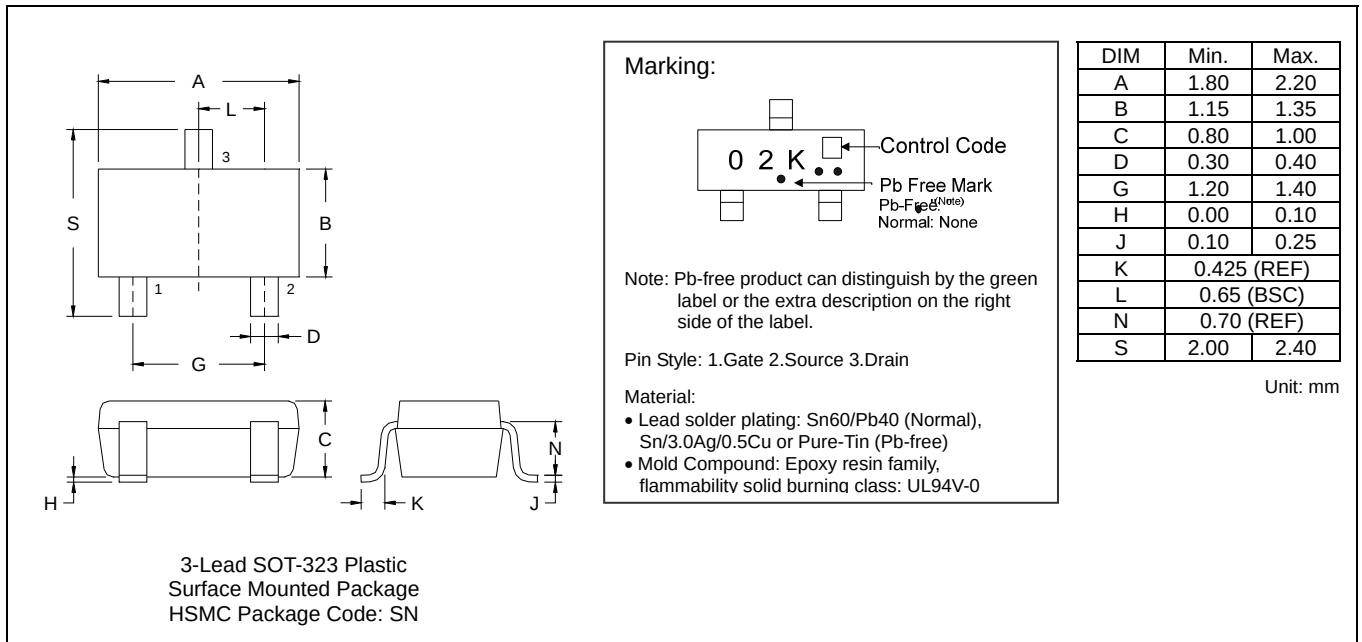


Characteristics Curve





SOT-323 (SC-70) Dimension



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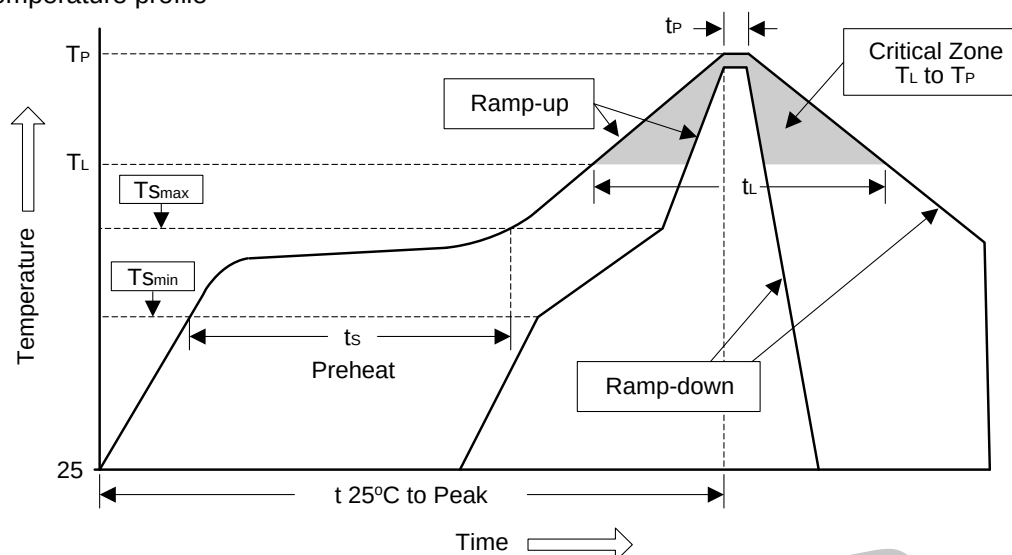
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Soldering Methods for HSMC's Products

1. Storage environment: Temperature=10°C~35°C Humidity=65%±15%
2. Reflow soldering of surface-mount devices

Figure 1: Temperature profile



Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Average ramp-up rate (T_L to T_P)	<3°C/sec	<3°C/sec
Preheat		
- Temperature Min (T_{Smin})	100°C	150°C
- Temperature Max (T_{Smax})	150°C	200°C
- Time (min to max) (t_s)	60~120 sec	60~180 sec
T_{Smax} to T_L		
- Ramp-up Rate	<3°C/sec	<3°C/sec
Time maintained above:		
- Temperature (T_L)	183°C	217°C
- Time (t_L)	60~150 sec	60~150 sec
Peak Temperature (T_P)	240°C +0/-5°C	260°C +0/-5°C
Time within 5°C of actual Peak Temperature (t_P)	10~30 sec	20~40 sec
Ramp-down Rate	<6°C/sec	<6°C/sec
Time 25°C to Peak Temperature	<6 minutes	<8 minutes

3. Flow (wave) soldering (solder dipping)

Products	Peak temperature	Dipping time
Pb devices.	245°C ±5°C	5sec ±1sec
Pb-Free devices.	260°C +0/-5°C	5sec ±1sec